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1-7-02
Attn:

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: **Kenji IMANISHI**

Serial No.: **Not Yet Assigned**

Filed: **October 19, 2001**

For: **A FIELD-EFFECT TRANSISTOR USING A GROUP III-V COMPOUND SEMICONDUCTOR**

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Date: October 19, 2001

Sir:

Prior to calculation of the filing fee and examination of this application, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 5 through 7 as follows:

5. (Amended) The high electron mobility transistor as described in claim 3, wherein the thickness of said first channel layer is 3~7 nm.

6. (Amended) The high electron mobility transistor as described in claim 3, wherein the thickness of said second channel layer is 10~20 nm.